



# N-Channel 100-V (D-S) 175 °C MOSFET

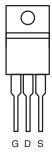
PRODUCT SUMMARY				
V <sub>(BR)DSS</sub> (V)	$r_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
100	0.030 at V <sub>GS</sub> = 10 V	40		
	0.034 at V <sub>GS</sub> = 6 V	37.5		

#### **FEATURES**

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature



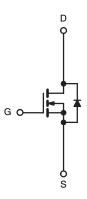




Top View

Ordering Information: SUP40N10-30

SUP40N10-30-E3 (Lead (Pb)-free)



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_C = 25$ °C, unless otherwise noted					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	100	V	
Gate-Source Voltage		V <sub>GS</sub>	V <sub>GS</sub> ± 20		
Continuous Drain Current (T <sub>J</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I-	40		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	23		
Pulsed Drain Current		I <sub>DM</sub>	75	_ A	
Avalanche Current		I <sub>AS</sub>	35		
Single Pulse Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	61	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	107 <sup>b</sup>	14/	
	T <sub>A</sub> = 25 °C <sup>c</sup>	$ P_D$ $-$	3.75	W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount <sup>c</sup>	- R <sub>thJA</sub>	40	°C/W
Sundion to Ambient	Free Air		62.5	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.4	

### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.

# Vishay Siliconix



<b>SPECIFICATIONS</b> $T_J = 25$	°C, unless	otherwise noted					
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1		
	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	μΑ	
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$			250	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	75			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		0.024	0.030	Ω	
	r · ·	V <sub>GS</sub> = 6 V, I <sub>D</sub> = 10 A		0.026	0.034		
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C			0.054		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C			0.067		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A	10			S	
Dynamic <sup>b</sup>	•						
Input Capacitance	C <sub>iss</sub>			2400		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		270			
Reverse Transfer Capacitance	C <sub>rss</sub>			90			
Total Gate Charge <sup>c</sup>	Qg			35	60	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 40 \text{ A}$		11			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			9			
Gate Resistance	$R_{g}$			1.7		Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			11	20	ns ns	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 1.25 $\Omega$ $I_D$ $\cong$ 40 A, $V_{GEN}$ = 10 V, $R_G$ = 2.5 $\Omega$		12	20		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			30	45		
Fall Time <sup>c</sup>	t <sub>f</sub>			12	20		
Source-Drain Diode Ratings and Cha	aracteristics	(T <sub>C</sub> = 25 °C) <sup>b</sup>		•	<b>'</b>		
Continuous Current	I <sub>S</sub>				40		
Pulsed Current	I <sub>SM</sub>				75	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_F = 30 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			60	100	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs		5	8	Α	
Reverse Recovery Charge	Q <sub>rr</sub>			0.15	0.4	μC	

#### Notes:

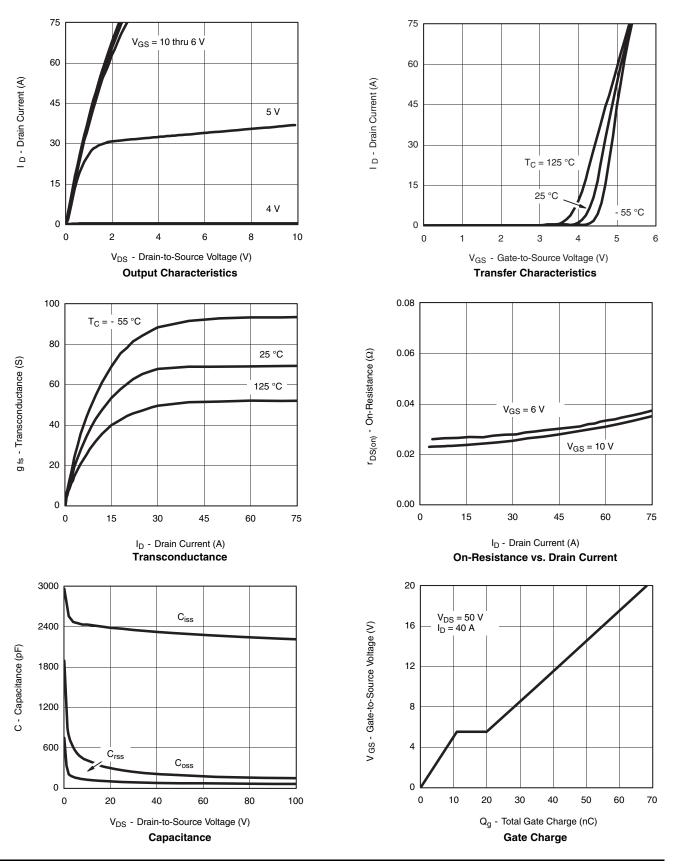
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





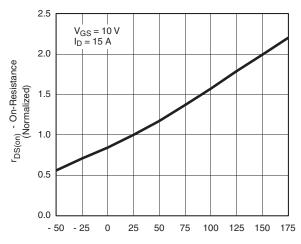
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



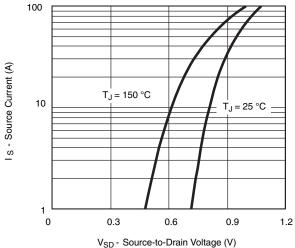
# Vishay Siliconix

# VISHAY.

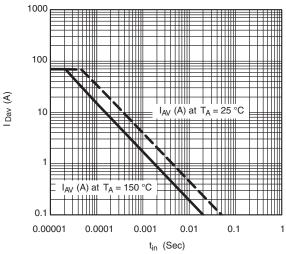
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



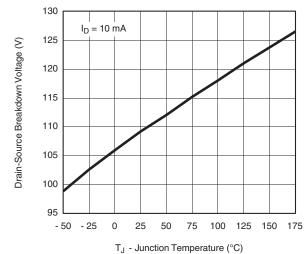
 $T_J$  - Junction Temperature (°C) **On-Resistance vs. Junction Temperature** 



Source-Drain Diode Forward Voltage



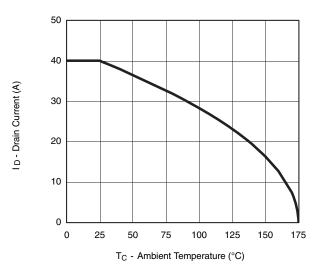
**Avalanche Current vs. Time** 



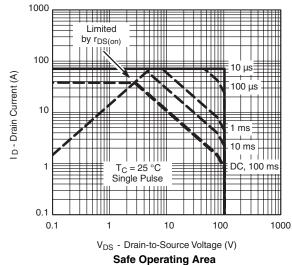
Drain-Source Breakdown Voltage vs. Junction Temperature



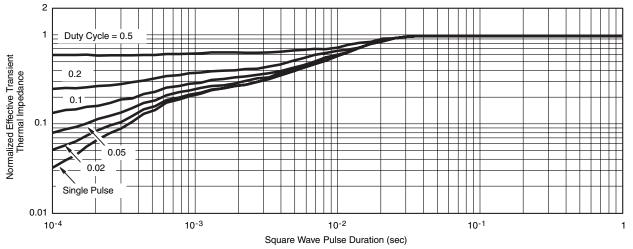
#### THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?72135">http://www.vishay.com/ppg?72135</a>.



## **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.